1 Characteristics

Table 2: Absolute maximum ratings (limiting values)

Symbol	Parame	Value	Unit		
I _{T(RMS)}	RMS on-state current (full sine wave	e)	T _c = 124 °C	12	А
	Non repetitive surge peak on-state o	t _p = 16.7 ms	95	A	
Ітѕм	T _j initial = 25 °C	t _p = 20 ms	90		
l²t	I ² t value for fusing		T _j initial = 25 °C	54	A ² s
dl/dt	Critical rate of rise of on-state currer $I_G = 2 \times I_{GT}$, tr $\leq 100 \text{ ns}$	100	A/µs		
λ/Λ/	Departitive peak off state voltage	T _j = 150 °C	600	V	
Vdrm/Vrrm	Repetitive peak off-state voltage	spellive peak on-state voltage		800	V
Vdsm/Vrsm	Non Repetitive peak off-state voltag	$t_p = 10 \text{ ms}$	900	V	
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 150 °C	4	А
P _{G(AV)}	Average gate power dissipation	1	W		
T _{stg}	Storage junction temperature range	-40 to +150	°C		
Tj	Operating junction temperature rang	-40 to +150	°C		

Table 3: Electrical characteristics (T_j = 25 °C, unless otherwise specified)

Symbol	Test conditions	Quadrants; Tj		Value	Unit
1	V_D = 12 V, R _L = 33 Ω	- -	Min.	1.75	mA
I _{GT}	$V_D = 12 \text{ V}, \text{ R}_L = 33 \Omega$	- -	Max.	35	mA
Vgt	V_D = 12 V, R _L = 33 Ω	- -	Max.	1.3	V
Vgd	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, T_j = 150 ^\circ\text{C}$	- -	Min.	0.2	V
١L	$I_G = 1.2 \text{ x } I_{GT}$	1 - 111	Max.	60	mA
IL.	IG = 1.2 x IGT	II	Max.	80	mA
IH ⁽¹⁾	I⊤ = 500 mA, gate open	Max.	40	mA	
dV/dt (1)	V _D = 536 V, gate open	T _j = 125 °C	Min.	2000	V/µs
	V _D = 402 V, gate open	T _j = 150 °C	Min.	1000	V/µs
(dl/dt)o(1)	Without anyther (d)/(dt) > 20)//up	T _j = 125 °C	Min.	12	A/ms
(dl/dt)c ⁽¹⁾	Without snubber, (dV/dt)c > 20 V/µs	T _j = 150 °C	Min.	6	A/ms

Notes:

 $^{(1)}\mbox{For both polarities of A2 referenced to A1.}$



Characteristics

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	Table 4: Static characteristics						
Symbol	Test conditions	Tj		Value	Unit		
Vtm ⁽¹⁾	$I_T = 17 \text{ A}, t_p = 380 \ \mu s$	25 °C	Max.	1.6	V		
Vто ⁽¹⁾	Threshold on-state voltage	150 °C	Max.	0.85	V		
R _D ⁽¹⁾	Dynamic resistance	150 °C	Max.	50	mΩ		
	V _{DRM} = V _{RRM} = 800 V	25 °C	Max.	5	μA		
Idrm/Irrm	$v_{\text{DRM}} = v_{\text{RRM}} = 800$ v	125°C	ividX.	1	mA		
	$V_{DRM} = V_{RRM} = 600 \text{ V}$	150 °C	Max.	3.1	mA		

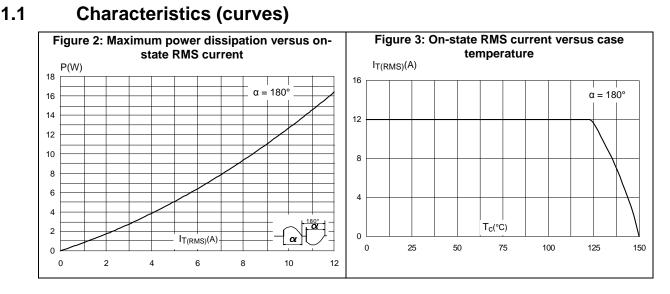
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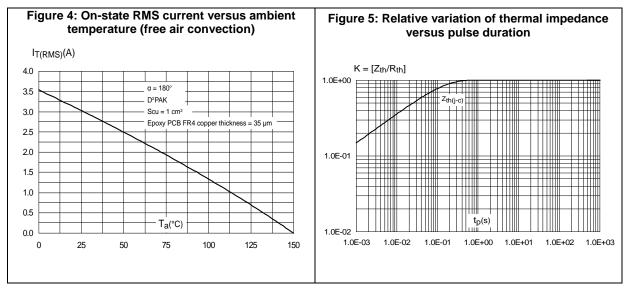
 $^{(1)}\mbox{For both polarities of A2 referenced to A1.}$

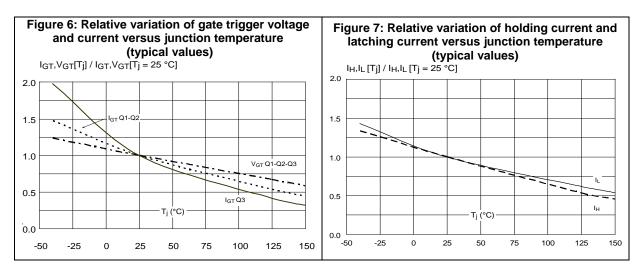
Table 5: Thermal resistance

Symbol	Parameter	Value	Unit		
R _{th(j-c)}	Junction to case (AC)	D²PAK	Max.	1.6	°C/W









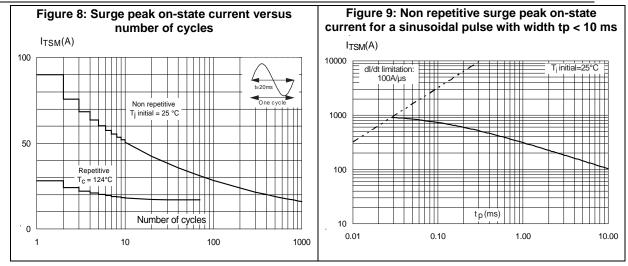
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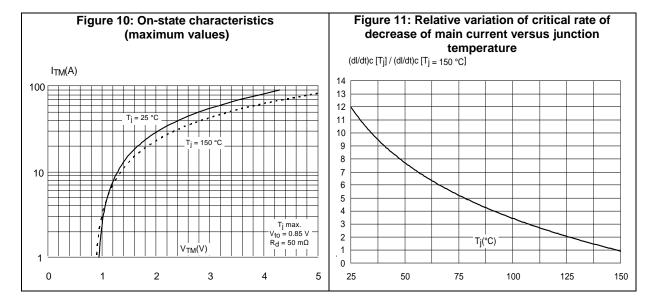
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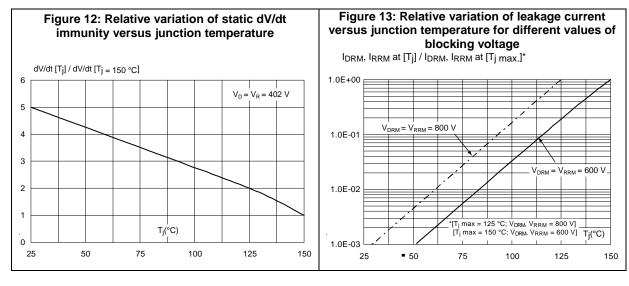


T1235T-8G

Characteristics







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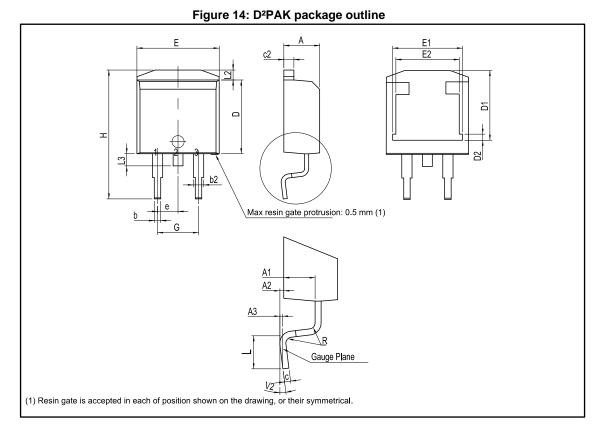
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2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

- ECOPACK[®]2 compliant
- Lead-free package leads finishing
- Molding compound resin is halogen-free and meets UL standard level V0

2.1 D²PAK package information



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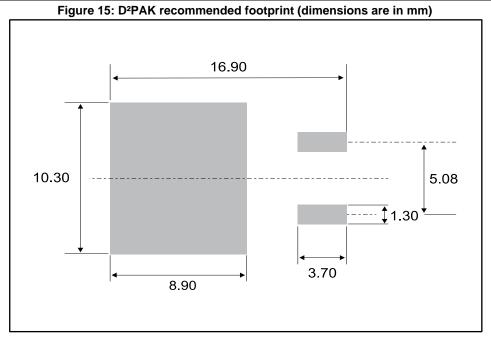
Package information

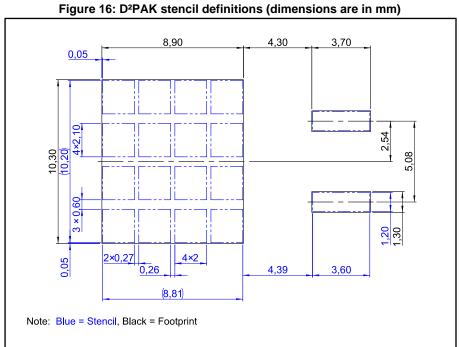
	Table 6: D ² PAK package mechanical data							
	Dimensions							
Ref.		Millimeters		Inches ⁽¹⁾				
	Min.	Тур.	Max.	Min.	Тур.	Max.		
А	4.30		4.60	0.1693		0.1811		
A1	2.49		2.69	0.0980		0.1059		
A2	0.03		0.23	0.0012		0.0091		
A3		0.25			0.0098			
b	0.70		0.93	0.0276		0.0366		
b2	1.25		1.7	0.0492		0.0669		
С	0.45		0.60	0.0177		0.0236		
c2	1.21		1.36	0.0476		0.0535		
D	8.95		9.35	0.3524		0.3681		
D1	7.50		8.00	0.2953		0.3150		
D2	1.30		1.70	0.0512		0.0669		
е	2.54			0.1				
E	10.00		10.28	0.3937		0.4047		
E1	8.30		8.70	0.3268		0.3425		
E2	6.85		7.25	0.2697		0.2854		
G	4.88		5.28	0.1921		0.2079		
Н	15		15.85	0.5906		0.6240		
L	1.78		2.28	0.0701		0.0898		
L2	1.27		1.40	0.0500		0.0551		
L3	1.40		1.75	0.0551		0.0689		
R		0.40			0.0157			
V2	0°		8°	0°		8°		

Notes:

 $\ensuremath{^{(1)}}\xspace$ Dimensions in inches are given for reference only







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3 Ordering information

Figure 17: 0	Drdering	information	scheme

Snubberless™ TRIAC			
RMS current			
12 = 12 A			
I _{GT} current			
35 = 35 mA			
Specific application			
T = increased (dl/dt) and dV/d	It producing reduc	ced I _{TSM}	
Voltage			
8 = 800 V			
Package			
G = D ² PAK			
Packing			
Blank = Tube			

Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
T1235T-8G-TR	T4005T 00	D²PAK	1.00 ~	1000	Tape and reel
T1235T-8G	T1235T-8G		1.38 g	50	Tube

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
19-Dec-2017	1	Initial release.



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